

ABSTRACT OF THE DISCLOSURE

Ferroelectric memory includes a hollow formed in a first insulation film. A lower electrode is formed in this hollow by sol-gel method including an application process due to a spin coat method. In this application process, a precursor solution is dripped on a surface of the first insulation film and splashed away due to centrifugal force. Due to this, a first conductive film to being formed has an increased film thickness at portion of the hollow where the precursor solution is ready to correct, or portion to be formed into a lower electrode, and a decreased film thickness at portion other than the hollow. Accordingly, it is satisfactory to etch only the hollow portion when forming a lower electrode by dry-etching the first conductive film.